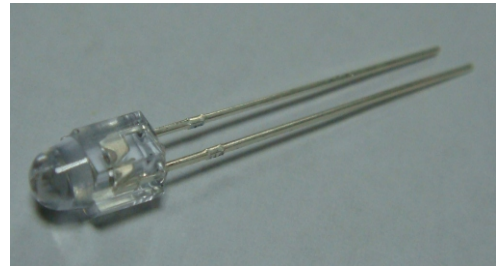
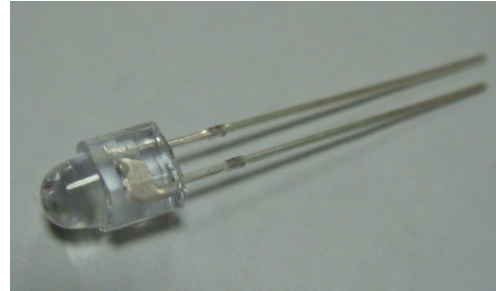




● Features:

- 1. Chip material: Silicon
- 2. Emitting color: Photo Diode
- 3. Lens Appearance: Water Clear
- 4. Long life-solid state reliability
- 5. IC compatible/Low current capability
- 6. RoHS compliant

● Package dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25\text{mm}$ (0.01") unless otherwise specified.
- 3. An epoxy meniscus may extend about 1.0mm down to the lead.
- 4. Specifications are subject to change without notice.

● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Test Condition	Symbol	P	Units
Reverse Breakdown Voltage		V_{BR}	60	V
Power Dissipation		P_D	100	mW
Operating Temperature		T_{OPR}	-40 to +80	$^\circ\text{C}$
Storage Temperature		T_{STG}	-40 to +85	$^\circ\text{C}$
Lead Soldering Temperature	1.60mm from body maximum 3 seconds	T_{SOL}	260	$^\circ\text{C}$



● Electrical And Optical Characteristics(Ta=25°C)

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Units
Light Current	V _R =5V H=5mw/cm ² @940nm	I _L	---	120	---	μA
Reverse Dark Current	V _R =10V H=0mw/cm ²	I _D	---	---	30	nA
Short Circuit Current	V _R =0V H=5mw/cm ² @940nm	I _{sc}	50	---	---	μA
Reverse Breakdown Voltage	I _R =100uA H=0mw/cm ²	V _{BR}	35	---	---	V
Open Circuit Voltage	V _R =0V H=5mw/cm ² @940nm	V _{oc}	---	0.4	---	V
Peak Sensing Wavelength		λ _p	---	940	---	nm
Rise Time Fall Time	R _L =50 Ω V _R =20V λ =850nm	t _r t _f	---	10	---	ns
Junction Capacitance	V _R =5V H=0mw/cm ² f=1.0MHZ	C _J	---	5.0	---	PF
Viewing Angle		2θ _½	---	30	---	deg.